NL27WZ125

Dual Buffer with 3-State Outputs

The NL27WZ125 is a high performance dual noninverting buffer operating from a 1.65 V to 5.5 V supply.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 2.7 ns t_{PD} at V_{CC} = 5 V (typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 24 mA at 3.0 V
- Available in US8, UDFN8 and UQFN8 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

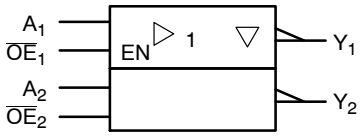
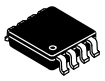


Figure 1. Logic Symbol

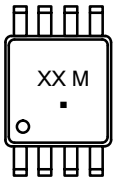
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MARKING DIAGRAMS

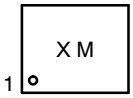


US8
US SUFFIX
CASE 493



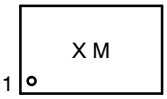


UDFN8, 1.45x1.0
MU3 SUFFIX
CASE 517BZ





UDFN8, 1.95x1.0
MU1 SUFFIX
CASE 517CA



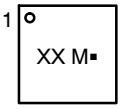


UQFN8, 1.4x1.2
MQ2 SUFFIX
CASE 523AS





UQFN8, 1.6x1.6
MQ1 SUFFIX
CASE 523AN

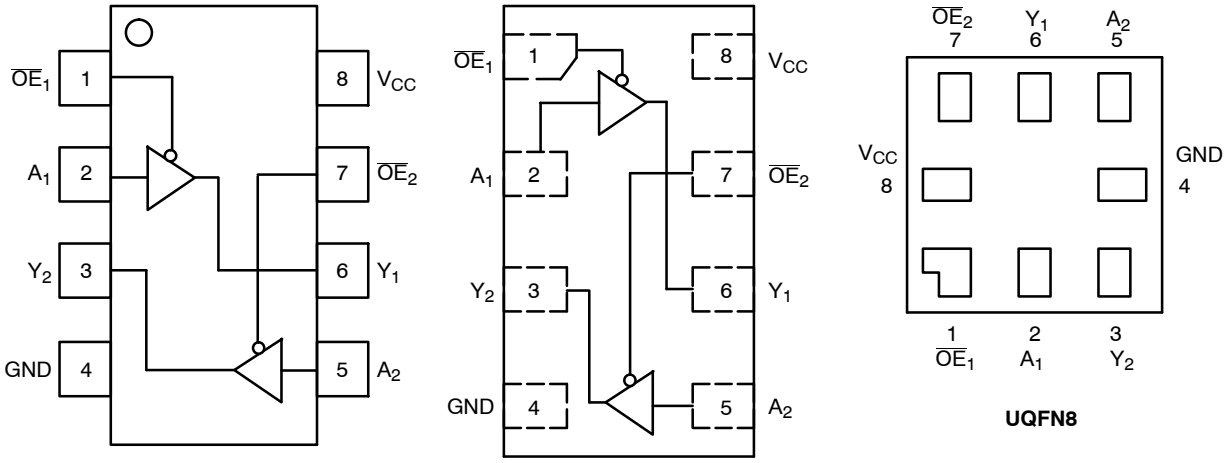


X, XX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 7 of this data sheet.

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US8 **UDFN8** **UQFN8**

Figure 2. Pinout

PIN ASSIGNMENT

Pin	Function
1	$\overline{OE}_1$
2	A_1
3	Y_2
4	GND
5	A_2
6	Y_2
7	$\overline{OE}_2$
8	V_{CC}

FUNCTION TABLE
$Y = \overline{AB}$

Input		Output
OE_n	B	Y_n
L	L	L
L	H	H
H	X	Z

X = Don't Care
n = 1, 2

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +6.5	V
V_{IN}	DC Input Voltage		−0.5 to +6.5	V
	DC Output Voltage	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} + 0.5 −0.5 to +6.5 −0.5 to +6.5	V
I_{IK}	DC Input Diode Current	V_{IN} < GND	−50	mA
I_{OK}	DC Output Diode Current	V_{OUT} < GND	−50	mA
I_{OUT}	DC Output Source/Sink Current		±50	mA
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 secs		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)	US8 UQFN8 UDFN8	250 208 111	°C/W
P_D	Power Dissipation in Still Air	US8 UDFN8 UQFN8	250 601 1127	mW
MSL	Moisture Sensitivity		Level 1	−
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	−
V_{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
$I_{Latchup}$	Latchup Performance (Note 4)		± 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri−stated.
2. Measured with minimum pad spacing on an FR4 board, using 10mm−by−1inch, 2 ounce copper trace no air flow.
3. HBM tested to ANSI/ESDA/JEDEC JS−001−2017. CDM tested to EIA/JESD22−C101−F. JEDEC recommends that ESD qualification to EIA/JESD22−A115−A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		1.65	5.5	V
V_{IN}	DC Input Voltage		0	5.5	V
V_{OUT}	DC Output Voltage	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	0 0 0	V_{CC} 5.5 5.5	
T_A	Operating Temperature Range		−55	+125	°C
t_r , t_f	Input Rise and Fall Time	V_{CC} = 1.65 V to 1.95 V V_{CC} = 2.3 V to 2.7 V V_{CC} = 3.0 V to 3.6 V V_{CC} = 4.5 V to 5.5 V	0 0 0 0	20 20 10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−55°C ≤ T_A ≤ 125°C		Units
				Min	Typ	Max	Min	Max	
V_{IH}	High−Level Input Voltage		1.65 to 1.95	0.65 V_{CC}	–	–	0.65 V_{CC}	–	V
			2.3 to 5.5	0.70 V_{CC}	–	–	0.70 V_{CC}	–	
V_{IL}	Low−Level Input Voltage		1.65 to 1.95	–	–	0.35 V_{CC}	–	0.35 V_{CC}	V
			2.3 to 5.5	–	–	0.30 V_{CC}	–	0.30 V_{CC}	
V_{OH}	High−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OH} = −100 μA I_{OH} = −4 mA I_{OH} = −8 mA I_{OH} = −12 mA I_{OH} = −16 mA I_{OH} = −24 mA I_{OH} = −32 mA	 1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	 V_{CC} − 0.1 1.29 1.9 2.2 2.4 2.3 3.8	 V_{CC} 1.4 2.1 2.4 2.7 2.5 4.0	 – – – – – – –	 V_{CC} − 0.1 1.29 1.9 2.2 2.4 2.3 3.8	 – – – – – – –	V
V_{OL}	Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OL} = 100 μA I_{OL} = 4 mA I_{OL} = 8 mA I_{OL} = 12 mA I_{OL} = 16 mA I_{OL} = 24 mA I_{OL} = 32 mA	 1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	 – – – – – – – –	 0.08 0.2 0.22 0.28 0.38 0.42	 0.1 0.24 0.3 0.4 0.4 0.55 0.55	 – – – – – – –	 0.1 0.24 0.3 0.4 0.4 0.55 0.55	V
I_{IN}	Input Leakage Current	V_{IN} = 5.5 V or GND	1.65 to 5.5	–	–	±0.1	–	±1.0	μA
I_{OFF}	Power Off Leakage Current	V_{IN} = 5.5 V or V_{OUT} = 5.5 V	0	–	–	1.0	–	10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5	–	–	1.0	–	10	μA
I_{OZ}	3−State Output Leakage	V_{IN} = V_{IL} or V_{IH} 0 V ≤ V_{OUT} ≤ 5.5 V	2.3 to 5.5	–	–	±0.5	–	±5	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

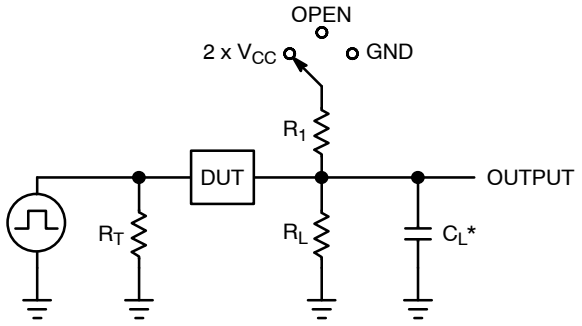
AC ELECTRICAL CHARACTERISTICS ($t_R = t_F = 3.0$ ns)

Symbol	Parameter	V_{CC} (V)	Condition	$T_A = 25°C$			$-55°C \le T_A \le 125°C$		Units
				Min	Typ	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay	1.8 ± 0.15	C_L = 15 pF, R_L = 1 MΩ R_1 = Open	–	6.0	12.0	–	13.0	ns
		2.5 ± 0.2		–	3.5	7.5	–	8.0	
		3.3 ± 0.3		–	2.6	5.2	–	5.5	
		5.0 ± 0.5		–	2.0	5.7	–	6.0	
		3.3 ± 0.3	C_L = 50 pF, R_L = 500 Ω R_1 = Open	–	3.0	4.5	–	4.8	
		5.0 ± 0.5		–	2.4	5.0	–	5.3	
t_{OSLH} t_{OSHL}	Output to Output Skew	3.3 ± 0.3	R_L = 500 Ω, C_L = 50 pF	–	0.08	1.0	–	1.0	ns
		5.0 ± 0.5		–	0.05	0.8	–	0.8	
t_{PZH} t_{PZL}	Output Enable Time	1.8 ± 0.15		–	6.5	14.0	–	15.0	ns
		2.5 ± 0.2		–	3.7	8.5	–	9.0	
		3.3 ± 0.3		–	2.8	6.2	–	6.5	
		5.0 ± 0.5		–	2.1	5.5	–	5.8	
t_{PHZ} t_{PLZ}	Output Enable Time	1.8 ± 0.15		–	4.2	12.0	–	13.0	ns
		2.5 ± 0.2		–	3.1	8.0	–	8.5	
		3.3 ± 0.3		–	2.6	5.7	–	6.0	
		5.0 ± 0.5		–	2.6	4.7	–	5.0	

CAPACITIVE CHARACTERISTICS ($t_R = t_F = 3.0$ ns)

Symbol	Parameter	Condition	Typical	Units
C_{IN}	Input Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	2.5	pF
C_{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	2.5	pF
C_{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 3.3 V, V_{IN} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	9 11	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



C_L includes probe and jig capacitance
R_T is Z_{OUT} of pulse generator (typically 50 Ω)
f = 1 MHz

Figure 3. Test Circuit

Test	Switch Position	C_L, pF	R_L, Ω	R_1, Ω
t_{PLH} / t_{PHL}	Open	See AC Characteristics Table		
t_{PLZ} / t_{PZL}	2 x V_{CC}	50	500	500
t_{PHZ} / t_{PZH}	GND	50	500	500

X = Don't Care

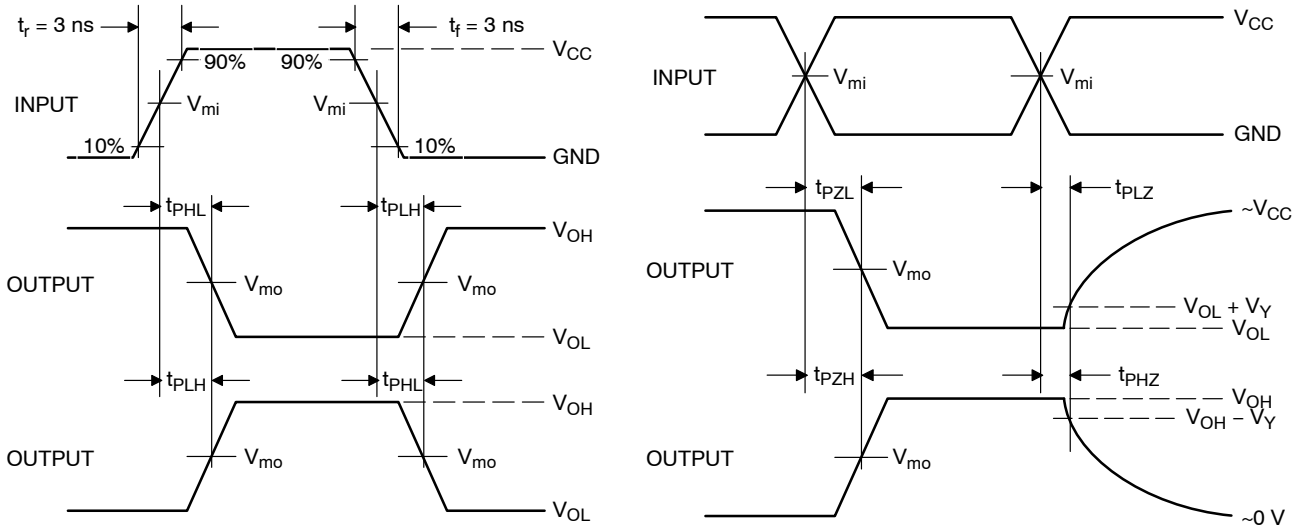


Figure 4. Switching Waveforms

V_{CC}, V	V_{mi}, V	V_{mo}, V		V_Y, V
		t_{PLH}, t_{PHL}	t_{PZL}, t_{PLZ}, t_{PZH}, t_{PHZ}	
1.65 to 1.95	V_{CC}/2	(V_{OH} – V_{OL})/2	V_{CC}/2	0.15
2.3 to 2.7	V_{CC}/2	(V_{OH} – V_{OL})/2	V_{CC}/2	0.15
3.0 to 3.6	V_{CC}/2	(V_{OH} – V_{OL})/2	V_{CC}/2	0.3
4.5 to 5.5	V_{CC}/2	(V_{OH} – V_{OL})/2	V_{CC}/2	0.3

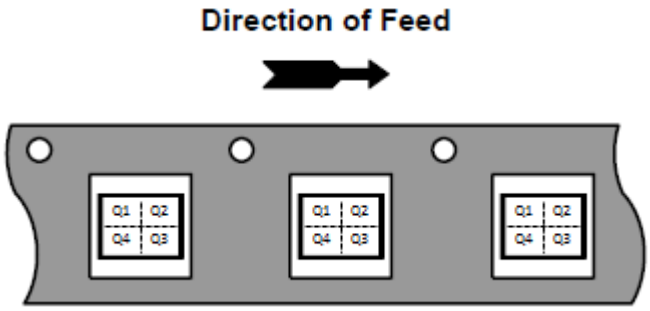
DEVICE ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping†
NL27WZ125USG	US8	M0	Q4	3000 / Tape & Reel
NLV27WZ125USG* (In Development)	US8	TBD	Q4	3000 / Tape & Reel
NL27WZ125MQ1TCG (In Development)	UQFN8, 1.6 x 1.6, 0.5P	TBD	TBD	3000 / Tape & Reel
NL27WZ125MU1TCG (In Development)	UDFN8, 1.95 x 1.0, 0.5P	TBD	TBD	3000 / Tape & Reel
NL27WZ125MU3TCG (In Development)	UDFN8, 1.45 x 1.0, 0.5P	TBD	TBD	3000 / Tape & Reel
NL27WZ125MQ2TCG (In Development)	UQFN8, 1.4 x 1.2, 0.5P	TBD	TBD	3000 / Tape & Reel
NL27WZ125 (In Development)	SM8	TBD	TBD	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

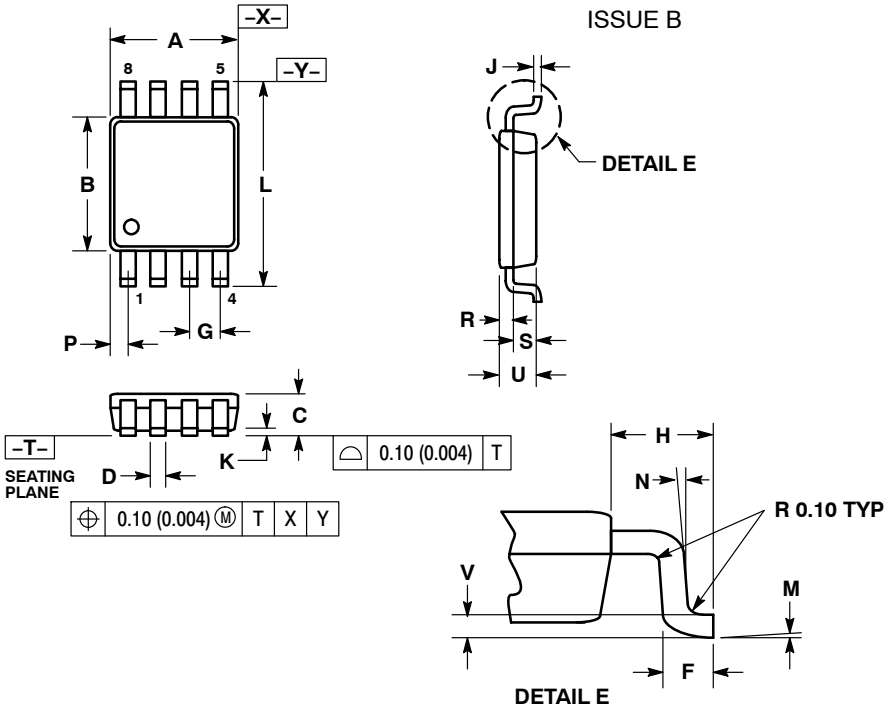
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

Pin 1 Orientation in Tape and Reel



PACKAGE DIMENSIONS

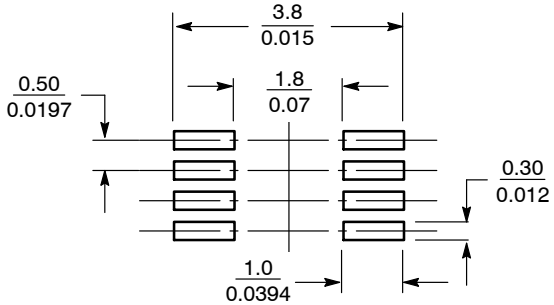
US8
US SUFFIX
CASE 493−02
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION “A” DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR. MOLD FLASH. PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.140 MM (0.0055”) PER SIDE.
4. DIMENSION “B” DOES NOT INCLUDE INTER−LEAD FLASH OR PROTRUSION. INTER−LEAD FLASH AND PROTRUSION SHALL NOT E3XCEED 0.140 (0.0055”) PER SIDE.
5. LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076−0.0203 MM. (300−800 “).
6. ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 (0.0002 “).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.90	2.10	0.075	0.083
B	2.20	2.40	0.087	0.094
C	0.60	0.90	0.024	0.035
D	0.17	0.25	0.007	0.010
F	0.20	0.35	0.008	0.014
G	0.50 BSC		0.020 BSC	
H	0.40 REF		0.016 REF	
J	0.10	0.18	0.004	0.007
K	0.00	0.10	0.000	0.004
L	3.00	3.20	0.118	0.126
M	0 °	6 °	0 °	6 °
N	5 °	10 °	5 °	10 °
P	0.23	0.34	0.010	0.013
R	0.23	0.33	0.009	0.013
S	0.37	0.47	0.015	0.019
U	0.60	0.80	0.024	0.031
V	0.12 BSC		0.005 BSC	

SOLDERING FOOTPRINT*

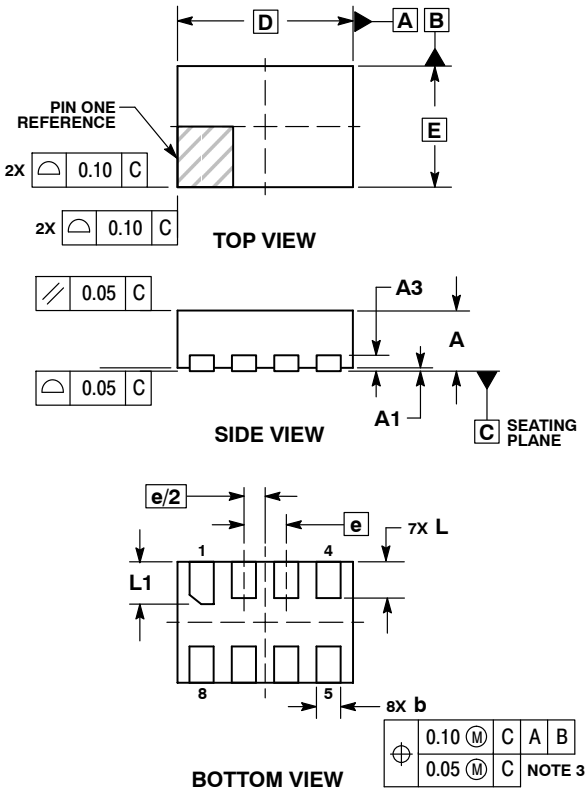


SCALE 8:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

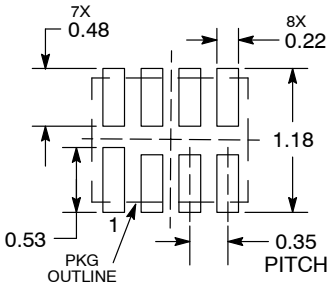
UDFN8, 1.45x1, 0.35P
CASE 517BZ
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.15	0.25
D	1.45 BSC	
E	1.00 BSC	
e	0.35 BSC	
L	0.25	0.35
L1	0.30	0.40

RECOMMENDED SOLDERING FOOTPRINT*

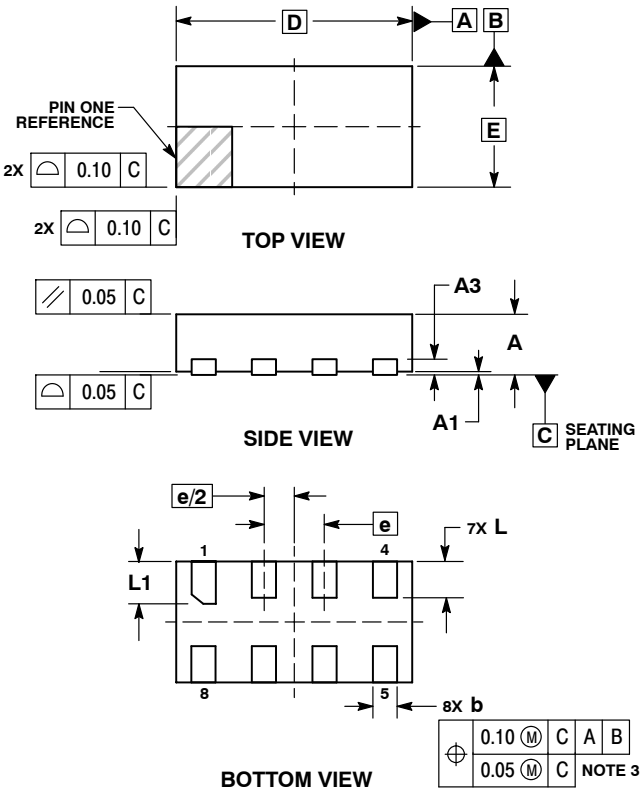


DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

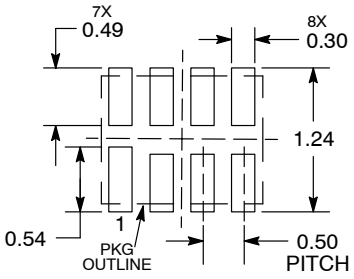
UDFN8, 1.95x1, 0.5P
CASE 517CA
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.15	0.25
D	1.95 BSC	
E	1.00 BSC	
e	0.50 BSC	
L	0.25	0.35
L1	0.30	0.40

RECOMMENDED SOLDERING FOOTPRINT*

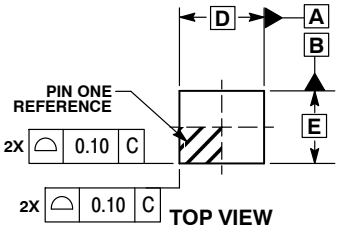


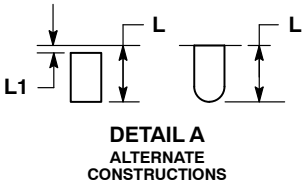
DIMENSIONS: MILLIMETERS

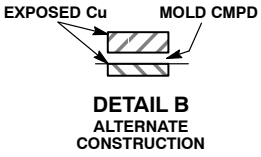
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

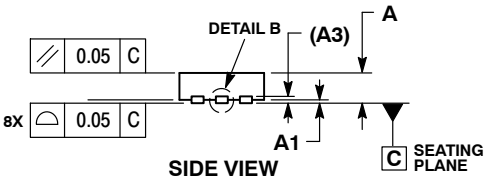
PACKAGE DIMENSIONS

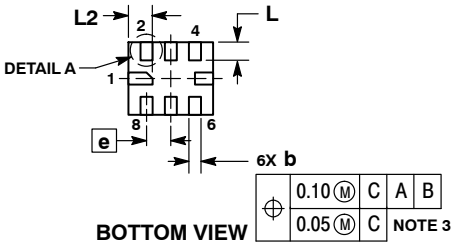
UQFN8, 1.4x1.2, 0.4P
CASE 523AS
ISSUE A







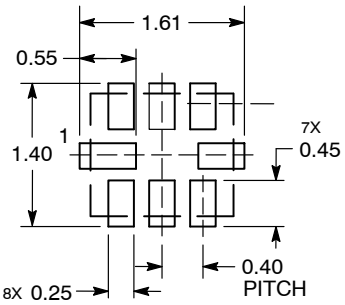




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.25 mm FROM THE TERMINAL TIP.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.15	0.25
D	1.40 BSC	
E	1.20 BSC	
e	0.40 BSC	
L	0.20	0.40
L1	----	0.15
L2	0.30	0.50

SOLDERING FOOTPRINT*

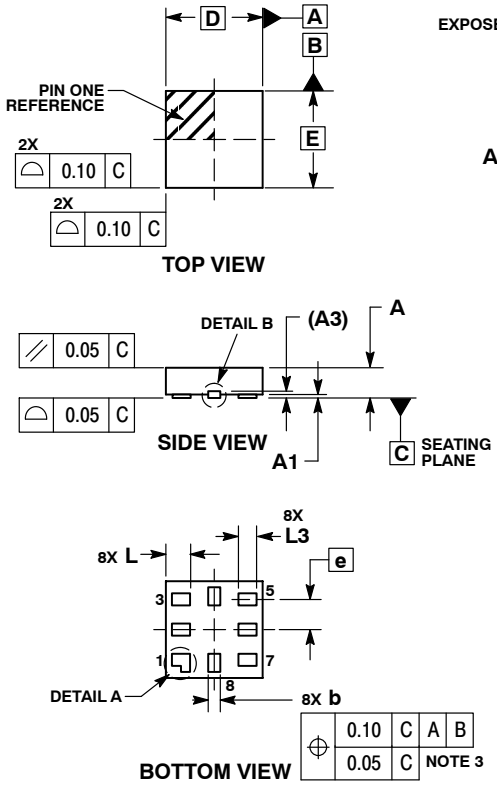


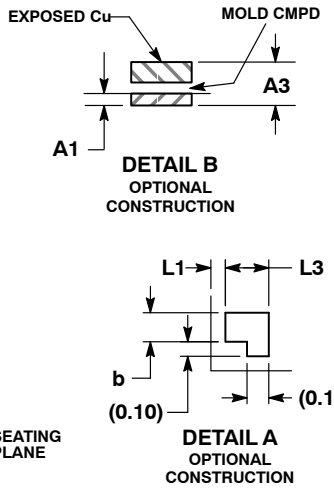
DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UQFN8, 1.6x1.6, 0.5P
CASE 523AN
ISSUE O

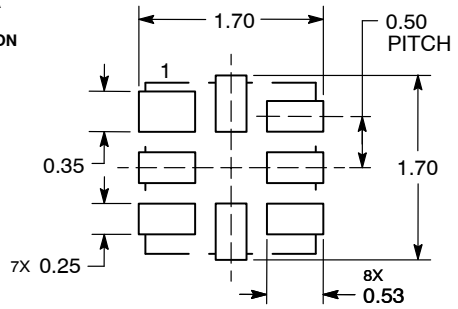




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.60
A1	0.00	0.05
A3	0.13 REF	
b	0.15	0.25
D	1.60 BSC	
E	1.60 BSC	
e	0.50 BSC	
L	0.35	0.45
L1	---	0.15
L3	0.25	0.35

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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